

N and P-Channel Enhancement Mode Power MOSFET

**Description**

The TGD4525 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge . The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

**General Features**

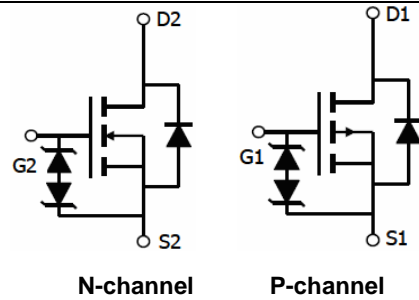
● **N-Channel**

- $V_{DS} = 40V, I_D = 7A$
- $R_{DS(ON)} < 24m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 38m\Omega @ V_{GS}=4.5V$

● **P-Channel**

- $V_{DS} = -40V, I_D = -5A$
- $R_{DS(ON)} < 38m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} < 50m\Omega @ V_{GS}=-4.5V$

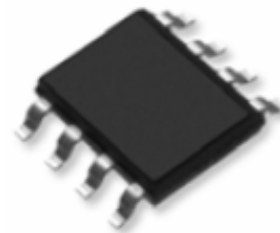
- High power and current handling capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



pin assignment



SOP-8 top view

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
TGD4525	TGD4525	SOP-8	Ø330mm	12mm	2500 units

**Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	$V_{DS}$	40	-40	V	
Gate-Source Voltage	$V_{GS}$	±12	±12	V	
Continuous Drain Current	$I_D$	$T_A=25^\circ C$	7	-5	A
		$T_A=70^\circ C$	5.8	-4.2	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	30	-30	A	
Maximum Power Dissipation	$P_D$	2.0	2.0	W	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	-55 To 150	°C	

**Thermal Characteristic**



Thermal Resistance,Junction-to-Ambient <sup>(Note2)</sup>	R <sub>θJA</sub>	N-Ch	62.5	°C/W
Thermal Resistance,Junction-to-Ambient <sup>(Note2)</sup>	R <sub>θJA</sub>	P-Ch	62.5	°C/W

**N-CH Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±10	μA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	-	19.5	24	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	29	38	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =6A	15	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note4)</sup>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	516	-	PF
Output Capacitance	C <sub>OSS</sub>		-	82	-	PF
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	43	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =2.5Ω V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	4.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	2.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	14.5	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3.5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =6A, V <sub>GS</sub> =10V	-	8.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.4	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =6A	-	0.8	1.2	V



**P-CH Electrical Characteristics ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-5A$	-	32	38	m $\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	-	39	50	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-5A$	10	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0MHz$	-	940	-	PF
Output Capacitance	$C_{oss}$		-	97	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	72	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	6.2	-	nS
Turn-on Rise Time	$t_r$		-	8.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	44.8	-	nS
Turn-Off Fall Time	$t_f$		-	16	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-20V, I_D=-5A$ $V_{GS}=-10V$	-	17	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.4	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.2	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-5A$	-	-	-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

N- Channel Typical Electrical and Thermal Characteristics (Curves)

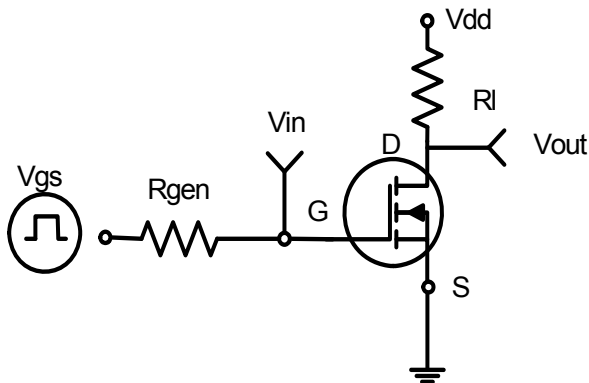


Figure 1: Switching Test Circuit

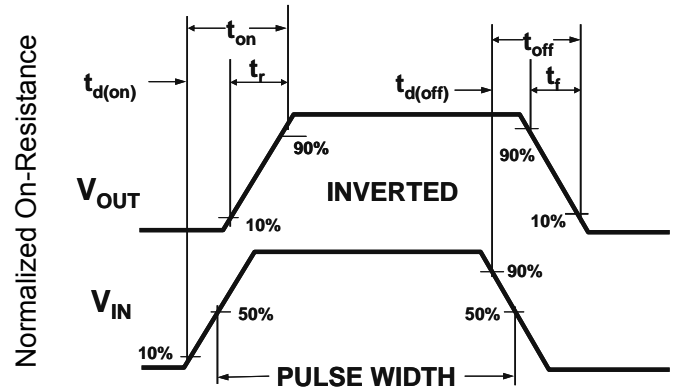


Figure 2: Switching Waveforms

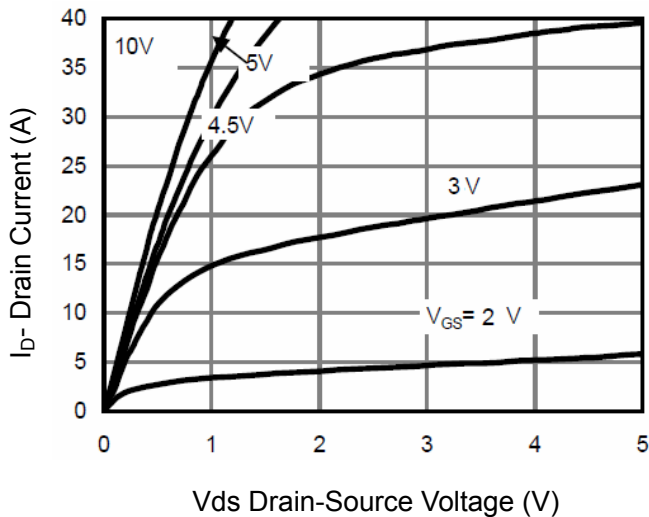


Figure 3 Output Characteristics

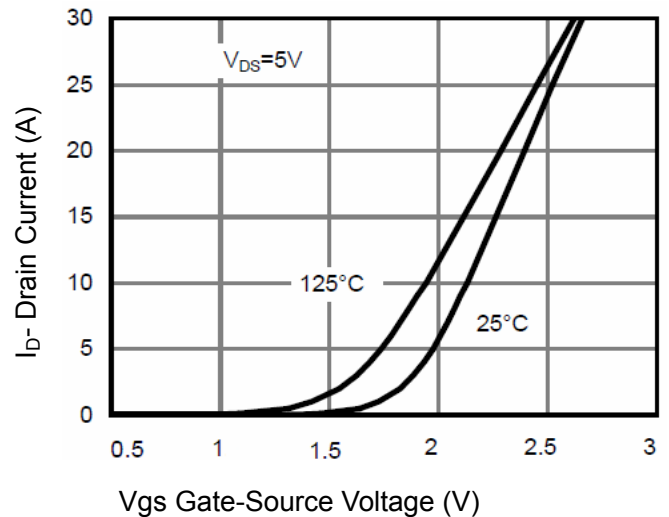


Figure 4 Transfer Characteristics

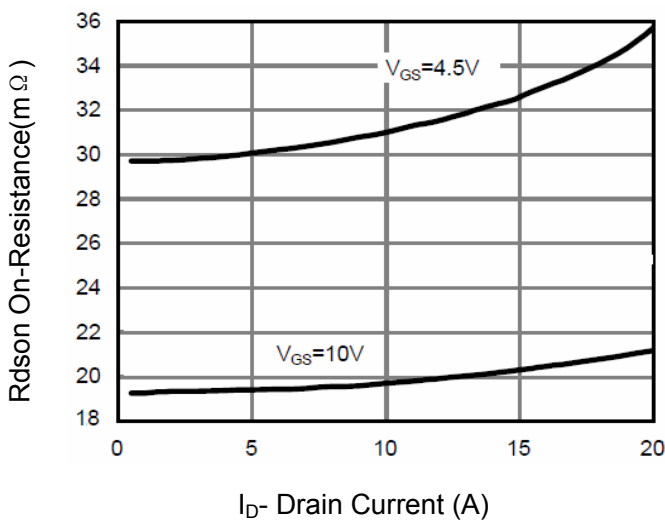


Figure 5 Drain-Source On-Resistance

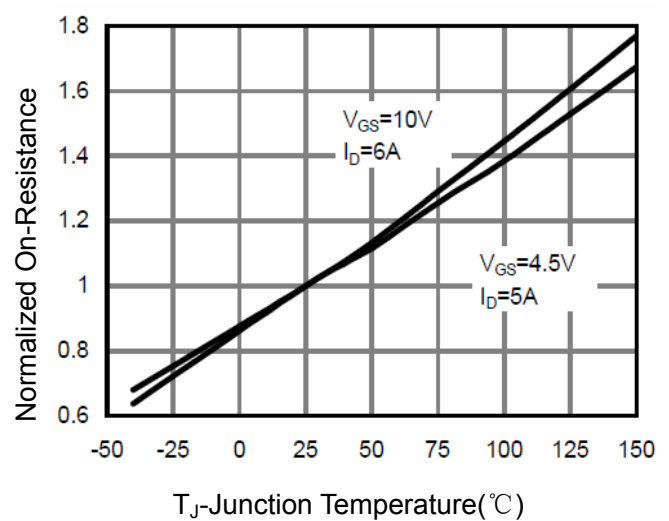
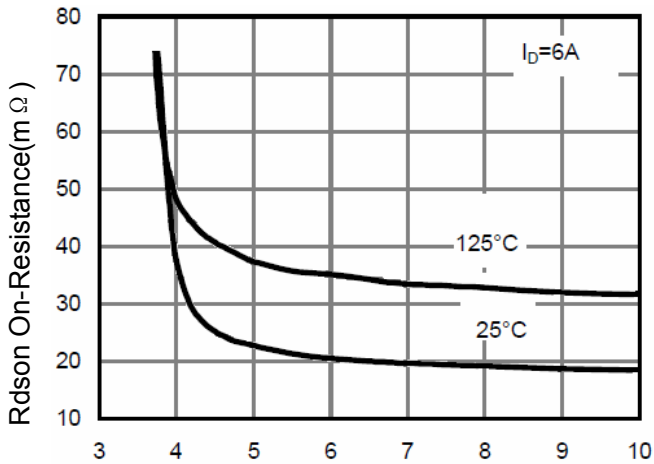
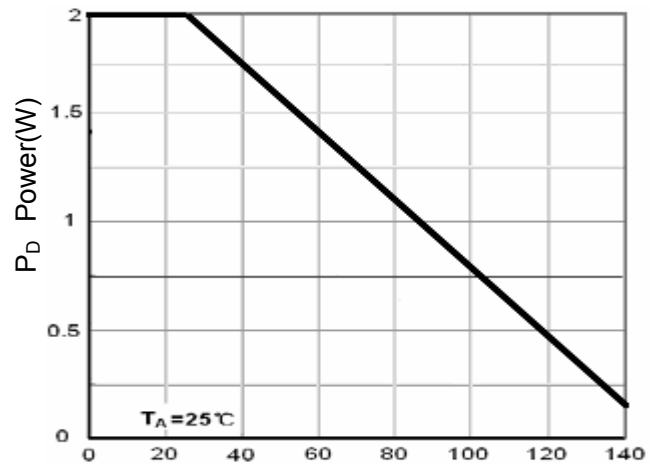


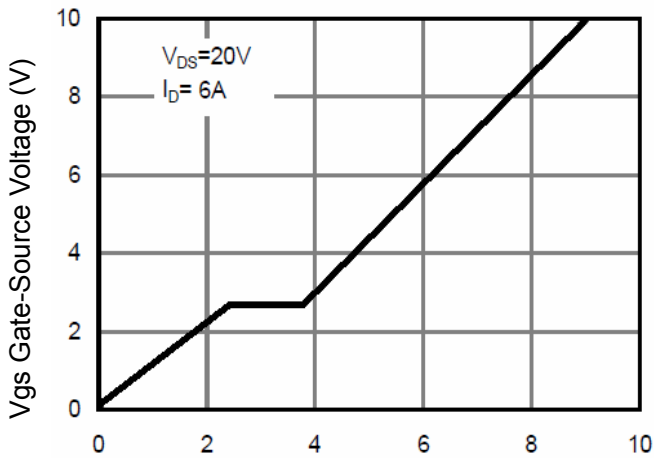
Figure 6 Drain-Source On-Resistance



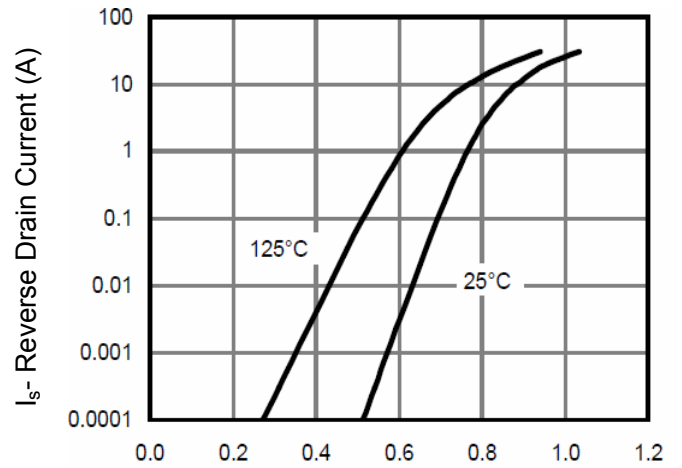
Vgs Gate-Source Voltage (V)  
**Figure 7 Rdson vs Vgs**



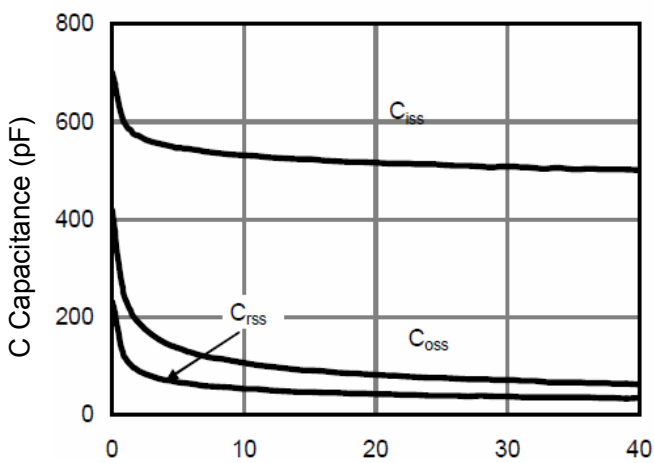
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 8 Power Dissipation**



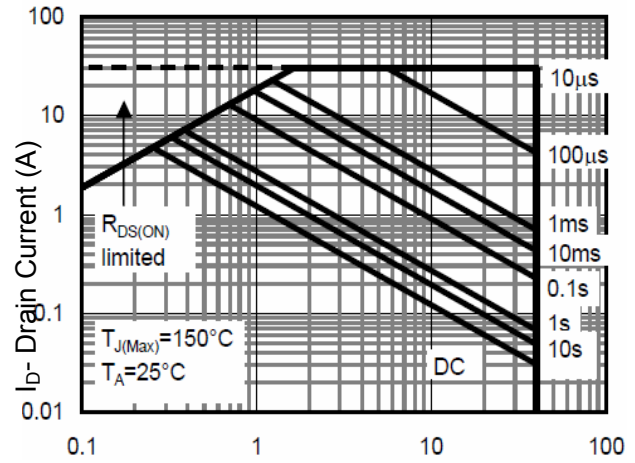
Qg Gate Charge (nC)  
**Figure 9 Gate Charge**



Vds Drain-Source Voltage (V)  
**Figure 10 Source- Drain Diode Forward**



Vds Drain-Source Voltage (V)  
**Figure 11 Capacitance vs Vds**



Vds Drain-Source Voltage (V)  
**Figure 12 Safe Operation Area**

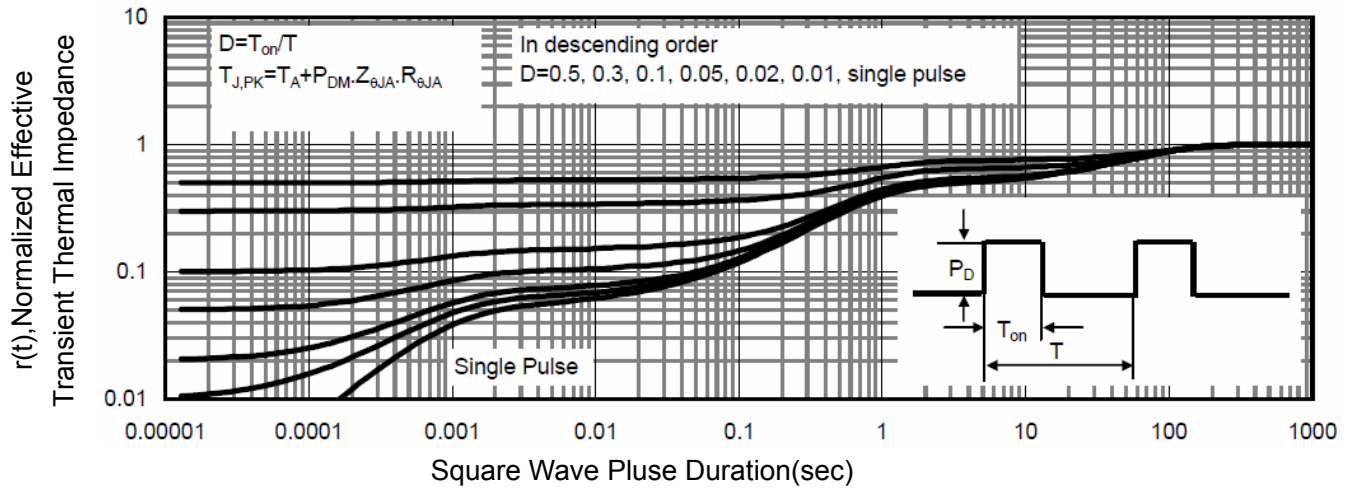
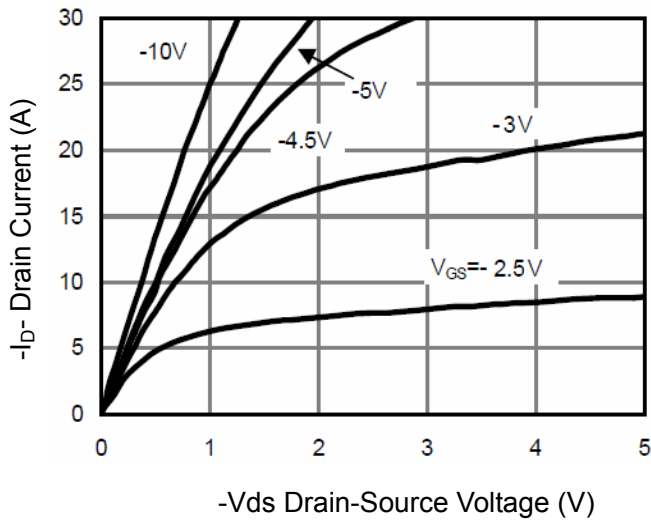
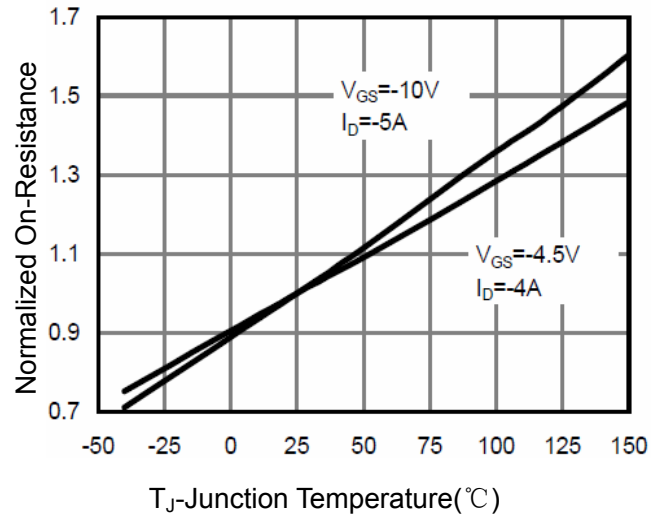


Figure 13 Normalized Maximum Transient Thermal Impedance

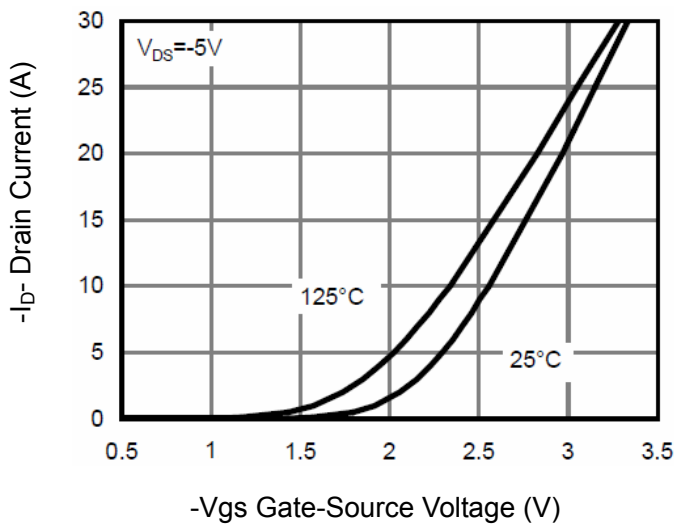
**P- Channel Typical Electrical and Thermal Characteristics (Curves)**



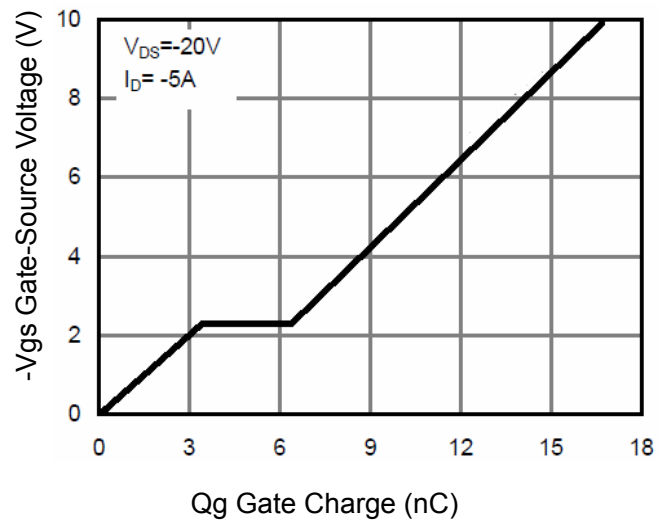
**Figure 1 Output Characteristics**



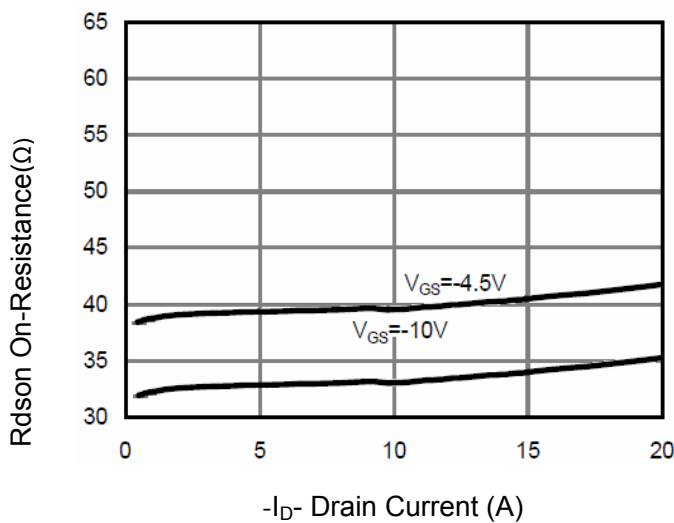
**Figure 4 Rdson-Junction Temperature**



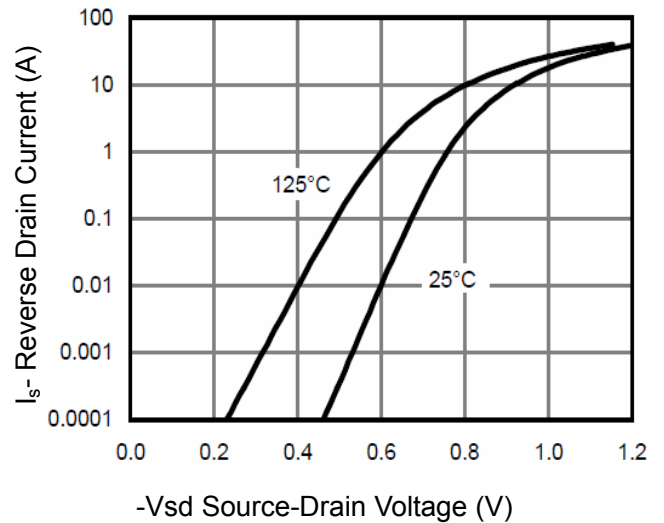
**Figure 2 Transfer Characteristics**



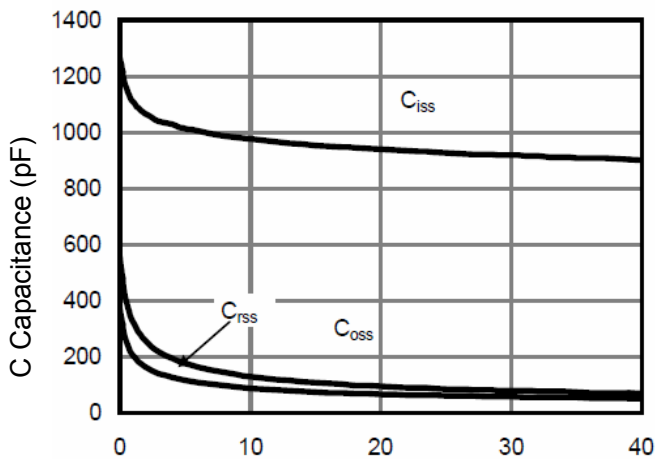
**Figure 5 Gate Charge**



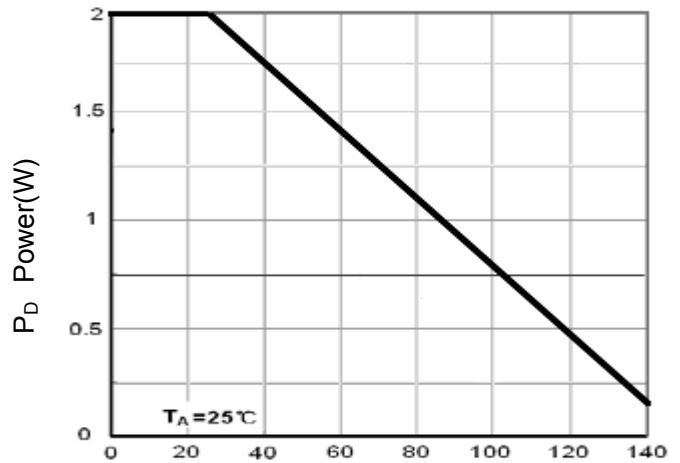
**Figure 3 Rdson- Drain Current**



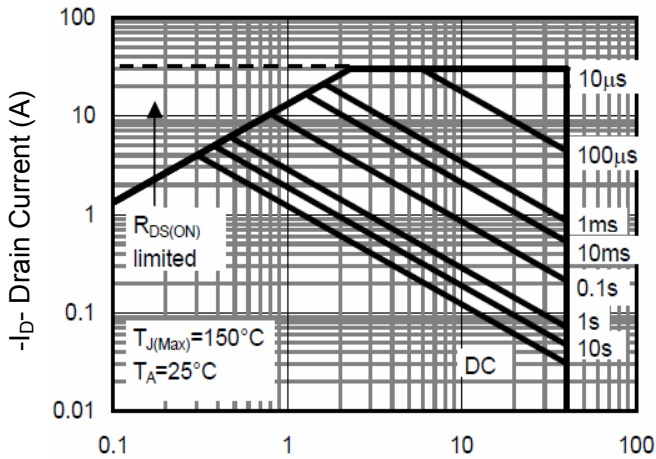
**Figure 6 Source- Drain Diode Forward**



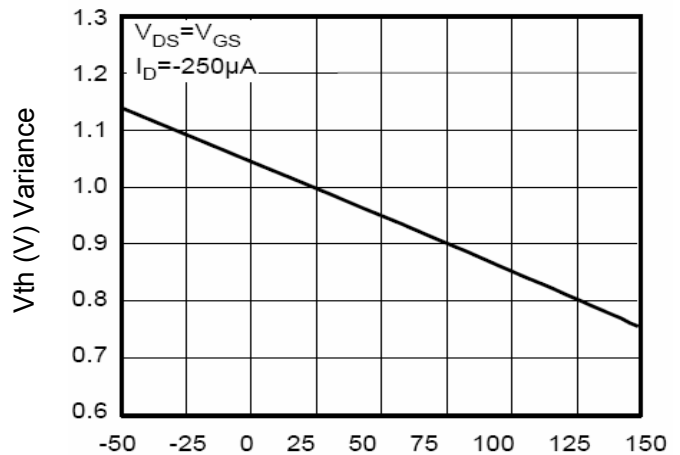
-Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



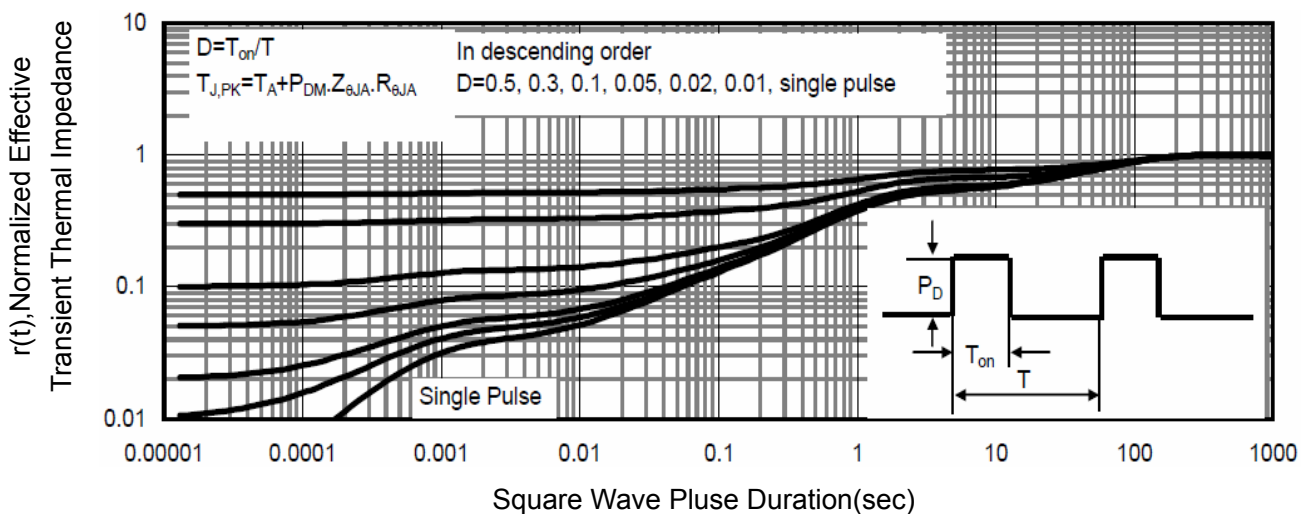
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 9 Power Dissipation**



-Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**



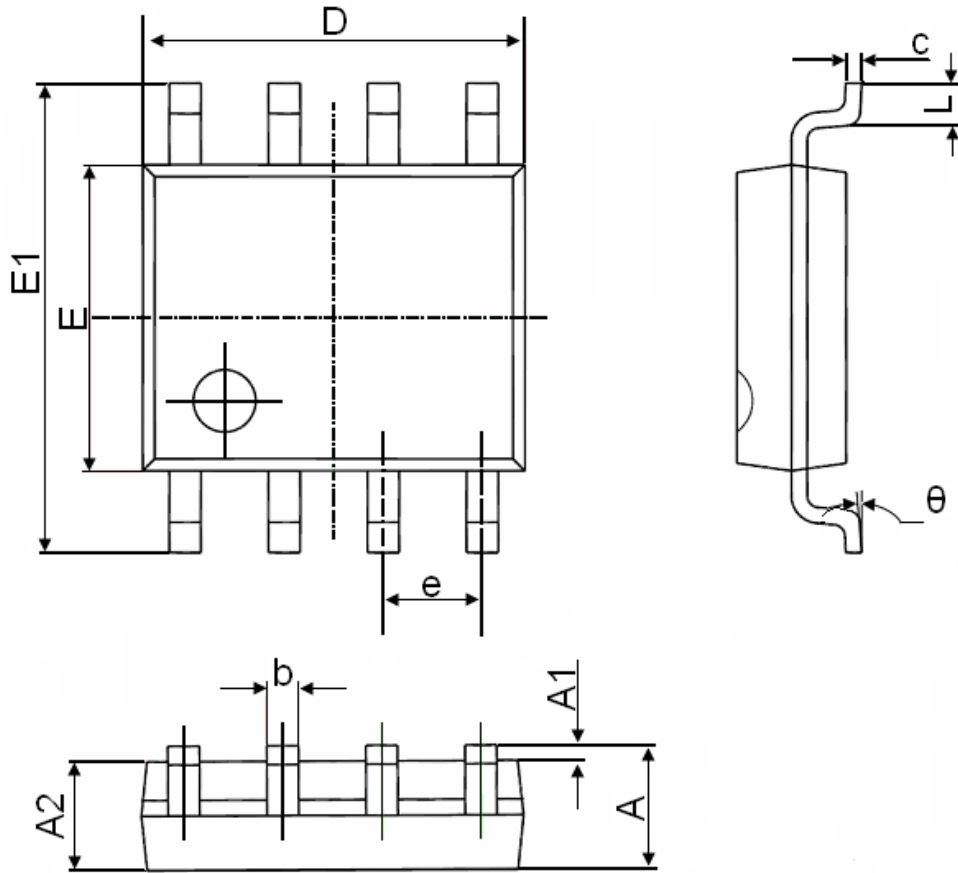
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 10 V<sub>GS(th)</sub> vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°